

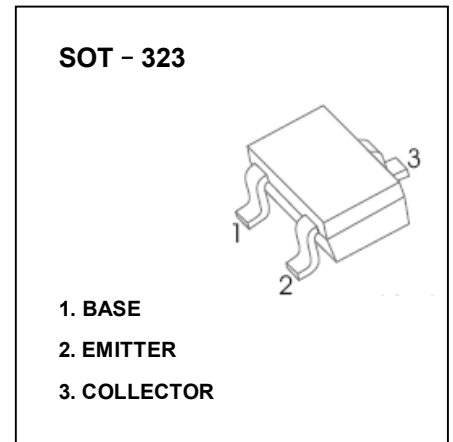
TRANSISTOR (NPN)

FEATURES

- High Breakdown Voltage
- Complements the 2SA1579

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|------------------|---|----------|------|
| V _{CB0} | Collector-Base Voltage | 120 | V |
| V _{CEO} | Collector-Emitter Voltage | 120 | V |
| V _{EBO} | Emitter-Base Voltage | 5 | V |
| I _C | Collector Current | 50 | mA |
| P _C | Collector Power Dissipation | 200 | mW |
| R _{θJA} | Thermal Resistance From Junction To Ambient | 625 | °C/W |
| T _J | Junction Temperature | 150 | °C |
| T _{stg} | Storage Temperature | -55~+150 | °C |



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|--------------------------------------|----------------------|---|-----|-----|-----|------|
| Collector-base breakdown voltage | V _{(BR)CBO} | I _C =50μA, I _E =0 | 120 | | | V |
| Collector-emitter breakdown voltage | V _{(BR)CEO} | I _C =1mA, I _B =0 | 120 | | | V |
| Emitter-base breakdown voltage | V _{(BR)EBO} | I _E =50μA, I _C =0 | 5 | | | V |
| Collector cut-off current | I _{CBO} | V _{CB} =100V, I _E =0 | | | 500 | nA |
| Emitter cut-off current | I _{EBO} | V _{EB} =4V, I _C =0 | | | 500 | nA |
| DC current gain | h _{FE} | V _{CE} =6V, I _C =2mA | 180 | | 560 | |
| Collector-emitter saturation voltage | V _{CE(sat)} | I _C =10mA, I _B =1mA | | | 0.5 | V |
| Transition frequency | f _T | V _{CE} =12V, I _C =2mA, f=100MHz | | 140 | | MHz |
| Collector output capacitance | C _{ob} | V _{CB} =12V, I _E =0, f=1MHz | | 2.5 | | pF |

CLASSIFICATION OF h_{FE}

| RANK | R | S |
|---------|-----------|-----------|
| RANGE | 180 - 390 | 270 - 560 |
| MARKING | TR | TS |